4400-103- Gp2508

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Docket: 0756-711

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| In re PATENT application of |) | 2501 |
|-----------------------------|---|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Shunpei YAMAZAKI, ET AL. |) | |
| Serial No. 07/852,517 |) | Art Unit: 2508 |
| Filed: March 17, 1992 |) | Examiner: M. Saadat |
| For: SEMICONDUCTOR MATER- |) | · 1101/9 |
| IAL AND METHOD FOR |) | My I |
| FORMING THE SAME AND |) | CERTIFICATE OF MAILING |
| THIN FILM TRANSISTOR |) | deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, pn 6/15/93 |

AMENDMENT

Honorable Commissioner of Patents and Trademarks

Washington, D.C. 20231

JUL 0 9 1993

GH. 192500

Sir:

In response to the Official Action of March 15, 1993, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 4, 18 and 20 as follows:

Claim 4, line 2, delete "or YAG laser".

18. (Amended) A thin film transistor comprising an [intrinsic or] at least substantially intrinsic semiconductor included in a channel of said thin 1 103 44.00 CK

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